4.1.2.5 - Appendix E: Specific PD's for Synchronous DRAM (SDRAM).

- 1.0 Introduction: This appendix describes the Presence Detects for Synchronous DRAM Modules with SPD revision level 2 (02h). These PD's are those referenced in the SPD standard document for "Specific Features". The following PD fields will occur, in the order presented, in table 1.1. Further descriptions of bytes 0 and 1 are found in the SPD standard. Further description of byte 2 is found in appendix A of the SPD standard. All unused entries will be coded as 00h or FFh. All unused bits in defined bytes will be coded as 0 except where noted.
- 1.1 Address map: The following is the SPD address map for SDRAM, which describes where the individual LUT-Entries/bytes will be held in the serial EEPROM:

Byte Number	Function described	Notes
0	Defines # bytes written into serial memory at module mfgr	1
1	Total # bytes of SPD memory device	2
2	Fundamental memory type (FPM, EDO, SDRAM) from appendix A	
3	# Row Addresses on this assembly	3
4	# Column Addresses on this assembly	
5	# Module Banks on this Assembly	
6	Data Width of this assembly	
7	Data Width continuation	
8	Voltage interface standard of this assembly	
9	SDRAM Cycle time at Max. Supported CAS Latency (CL), CL=X	4
10	SDRAM Access from Clock at CL=X	4
11	DIMM Configuration type (Non-parity, Parity, ECC)	
12	Refresh Rate/Type	4,5
13	SDRAM width, Primary DRAM	
14	Error Checking SDRAM data width	
15	Minimum Clock Delay, Back to Back Random Column Addresses	
16	Burst Lengths Supported	
17	# Banks on Each SDRAM device	4
18	CAS# Latencies Supported	4
19	CS# Latency	4
20	Write Latency	4
21	SDRAM Module Attributes	· ·
22	SDRAM Device Attributes: General	
23	Minimum Clock Cycle Time at CL X-1	4
24	Maximum Data Access Time from Clock @ CL X-1	4
25	Minimum Clock Cycle Time at CL X-2	4
26	Maximum Data Access Time from Clock @ CL X-2	4
27	Minimum Row Precharge Time	4
28	Minimum Row Active to Row Active delay	4
29	Minimum RAS to CAS delay	4
30	Minimum RAS Pulse Width	4
31	Module Bank Density	<u>'</u>
32	Address and Command Setup time before Clock	6
33	Address and Command Hold time after Clock	6
34	Data Input Setup Time before Clock	6
35	Data Input Hold Time after Clock	6
36-40	Reserved for VCSDRAM	- 0
41	Minimum Bank Cycle Time (tRC)	6
42-61	Superset Information (may be used in future)	0
62	SPD Revision	
63	Checksum for bytes 0-62	
64-71	Manufacturers JEDEC ID code per JEP-106E	
72	Manufacturing location	
73-90	Manufacturing location Manufacturer's Part Number	
91-92	Revision Code Medula Manufacturing Year	
93	Module Manufacturing Year	
94	Module Manufacturing Week	
95-98	Assembly Serial Number	9
99-125	Manufacturer Specific Data	7
126-127	Vendor Specific	7
128-255	Open for Customer use.	8

notes:

- 1) This will be programmed as 128 bytes for the 168 pin DIMM Module.
- High order bit defines if assembly has "redundant" addressing (if set to "1", highest order RAS# address must be re-sent as highest order CAS# address.)
- 4) From data sheet.
- 5) High order bit (MSB) is Self Refresh 'flag'. If Bit seven is "1", assembly supports self refresh.
- 6) The JEDEC spec. specifies that these bytes are optional for 66MHz applications. If they are not included then the SPD revision level (byte 62) is set at revision 1 (01h).
- 7) The JEDEC spec specifies that these bytes are optional.
- 8) Module suppliers will need to assure that these bytes are open for reads/writes by Customer.
- 9) Bytes 95-98 must be coded such that bytes 64-72 and 93-98 will result in a unique serial number. .
- 2.0 For Reference, Bytes 1-3. Descriptions of bytes 1 and 2 can be found in the main body of the SPD standard, and byte 3 is detailed in appendix A to this standard. For reference and convenience, applicable portions of their descriptions are presented again:
- 2.1 BYTE 0, From General SPD Standard, Number of Bytes used by Module Manufacturer: This field describes the total number of bytes used by the module manufacturer for the SPD data and any (optional) specific supplier information. The byte count includes the fields for all required and optional data.

Number SPD Bytes	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
3	0	0	0	0	0	0	1	1
4	0	0	0	0	0	1	0	0
5	0	0	0	0	0	1	0	1
6	0	0	0	0	0	1	1	0
7	0	0	0	0	0	1	1	1
8	0	0	0	0	1	0	0	0
9	0	0	0	0	1	0	0	1
10	0	0	0	0	1	0	1	0
11	0	0	0	0	1	0	1	1
								•
128	1	0	0	0	0	0	0	0
254	1	1	1	1	1	1	1	0
255	1	1	1	1	1	1	1	1

2.2 Byte 1, From General SPD Standard, Total SPD Memory Size: This field describes the total size of the serial memory used to hold the Serial Presence Detect data. The following lookup table describes the possible serial memory densities (in bytes) along with the corresponding descriptor:

Serial Memory Density	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Invalid	0	0	0	0	0	0	0	0
2 Bytes	0	0	0	0	0	0	0	1
4 Bytes	0	0	0	0	0	0	1	0
8 Bytes	0	0	0	0	0	0	1	1
16 Bytes	0	0	0	0	0	1	0	0
32 Bytes	0	0	0	0	0	1	0	1
64 Bytes	0	0	0	0	0	1	1	0
128 Bytes	0	0	0	0	0	1	1	1
256 Bytes	0	0	0	0	1	0	0	0
512 Bytes	0	0	0	0	1	0	0	1
1024 Bytes	0	0	0	0	1	0	1	0
2048 Bytes	0	0	0	0	1	0	1	1
4096 Bytes	0	0	0	0	1	1	0	0
8192 Bytes	0	0	0	0	1	1	0	1
16384 Bytes	0	0	0	0	1	1	1	0
	1	1	1	1	1	1	1	0
	1	1	1	1	1	1	1	1

2.3 Byte 2, From Appendix A, Memory Type: This byte describes the fundamental memory type (or technology) implemented on the module. See Appendix A for the complete list of memory types:

Fundamental Mem. Type	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
SDR SDRAM	0	0	0	0	0	1	0	0
		•						
.DDR SDRAM	0	0	0	0	0	1	1	1

- 3.0 Data Type(s): Even though many of the PD's seem to be binary numbers representing the feature they are describing, they are considered Look Up Table (LUT) entries.
- 4.0 The following PD bytes are those specific to modules implementing Synchronous DRAM technology. Note that these full descriptions start at byte 3 below and are not covered in the main body of the SPD standard since they are specific to a given fundamental memory type/technology
- 4.1 Byte 3, Number of ROW Addresses: This field describes the Row addressing on the module. If there is one physical bank on the module OR if there are two physical banks of the same size and organization, then Bits 0-3 are used to represent the number of row addresses for each physical bank. If the module has two physical banks of asymmetric size, then Bits 0-3 represent the number of row addresses for physical bank 1 and Bits 4-7 represent the number of row addresses for physical bank 2. Note that these do not include the Bank Address pin since physical bank selection on DIMM modules is asserted on dedicated BA (Bank Address) pins. Also note that if the module employs redundant addressing, then it is denoted in Byte 21, Bit 6. Examples of Byte 3 implementation include:

	# Row Addr	# Row Addr	Module	Discrete	Byte 3
#Banks	Bank 1	Bank2	Orgainzation	Used	Contents
1	11,RA0-RA10	N/A	2Mx64	2Mx8	0000 1011
2	11,RA0-RA10	11,RA0-RA10	2x2Mx64	2Mx8	0000 1011
2	11,RA0-RA10	11,RA0-RA10	2Mx64 & 1Mx64	2Mx8 & 1Mx16	1011 1011

					Table Subfield A: No. of Row addresses on Bank 1 -OR- No. of Row addresses on Bank 1 and 2 if both banks have the same depth, Bits 0-3				
# Row Addr					Bit 3	Bit 2	Bit 1	Bit 0	
Undefined					0	0	0	0	
1/16					0	0	0	1	
2/17					0	0	1	0	
:					:	:	:	:	
7	See Sub	field B			0	1	1	1	
8					1	0	0	0	
9					1	0	0	1	
10					1	0	1	0	
11					1	0	1	1	
12					1	1	0	0	
13					1	1	0	1	
14					1	1	1	0	
15					1	1	1	1	
	ad		lumber of I n Bank 2 (if , Bits 4-7						
# Row Addr	Bit 7	Bit 6	Bit5	Bit 4	1				
No 2 nd Asymet-	0	0	0	0	1				
1/16 rical bank	0	0	0	1					
2/17	0	0	1	0	1				
:	:	:	:	:	1				
7	0	1	1	1	1	See	Subfield	Α	
8	1	0	0	0	1				
9	1	0	0	1	1				
10	1	0	1	0	1				
11	1	0	1	1	1				
12	1	1	0	0	1				
13	1	1	0	1	1				
14	1	1	1	0	1				
15	1	1	1	1	1				

4.2 Byte 4, Number of Column Addresses: This field describes the Column addressing on the module. If there is one physical bank on the module OR if there are two physical banks of the same size, then Bits 0–3 are used to represent the number of column addresses for each physical bank. If the module has two physical banks of asymmetric size, then Bits 0–3 represent the number of column addresses for physical bank 1 and Bits 4–7 represent the number of column addresses for physical bank 2. For example:

	# Col Addr	# Col AddrModule	Discrete		Byte 3
#Banks	Bank 1	Bank2	Organization	Used	Contents
1	9,CA0-CA8	N/A	2Mx64	2Mx8	0000 1001
2	9,CA0-CA8	9,CA0-CA8	2x2Mx64	2Mx8	0000 1001
2	9,CA0-CA8	8,CA0-CA7	2Mx64 & 1Mx64	2Mx8 & 1Mx16	1000 1001

					Bank 1 -	ield A: No. of OR- No. of Ond 2 if both bo	Column addr anks same d	esses on	
# Column Addr					Bit 3	Bit 2	Bit 1	Bit 0	
Undefined					0	0	0	0	
1/16					0	0	0	1	
2/17					0	0	1	0	
÷					:	:	:	:	
7		See Su	bfield B		0	1	1	1	
8					1	0	0	0	
9					1	0	0	1	
10					1	0	1	0	
11					1	0	1	1	
12					1	1	0	0	
13					1	1	0	1	
14					1	1	1	0	
15					1	1	1	1	
		n Bank 2 (it	mber of Co f different fr ts 4-7						
# Column Addr	Bit 7	Bit 6	Bit 5	Bit 4					
No 2 nd Asymmetri- cal bank	0	0	0	0					
1/16	0	0	0	1					
2/17	0	0	1	0					
:	:	:	:	:					
7	0	1	1	1		See Su	bfield A		
8	1	0	0	0					
9	1	0	0	1					
10	1	0	1	0					
11	1	0	1	1	1				
12	1	1	0	0					
13	1	1	0	1					
14	1	1	1	0					
15	1	1	1	1					

4.3 Byte 5, Number of Banks on module: This field describes the number of physical banks on the SDRAM Module. This is not to be confused with the number of logical banks on a given SDRAM device which are defined in Byte 17:

Number of Banks	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
3	0	0	0	0	0	0	1	1
4	0	0	0	0	0	1	0	0
5	0	0	0	0	0	1	0	1
6	0	0	0	0	0	1	1	0
7	0	0	0	0	0	1	1	1
8	0	0	0	0	1	0	0	0
9	0	0	0	0	1	0	0	1
10	0	0	0	0	1	0	1	0
11	0	0	0	0	1	0	1	1
12	0	0	0	0	1	1	0	0
13	0	0	0	0	1	1	0	1
14	0	0	0	0	1	1	1	0
254	1	1	1	1	1	1	1	0
255	1	1	1	1	1	1	1	1

4.4 Bytes 6 & 7, Module Data Width: Bytes 6 and 7 are used to designate the module's data width. The data width is presented as a 16 bit word; Bit 0 of byte 6 becomes the LSB of the 16 bit width identifier and Bit 7 of byte 7 becomes the MSB. Consequently, if the module has a width of less than 255 Bits wide, byte 7 will be 00h. If the data width is 256 Bits or higher, byte 7 is used in conjunction with byte 6 to designate the total module width. For example, if the module's

data width is:	then byte 7 is	and byte 6 is:
64	0000 0000	0100 0000
72	0000 0000	0100 1000
80	0000 0000	0101 0000
576	0000 0010	0100 0000

4.4.1 Byte 6:

Data Width	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
3	0	0	0	0	0	0	1	1
								-
32	0	0	1	0	0	0	0	0
	•		•					
36	0	0	1	0	0	1	0	0
64	0	1	0	0	0	0	0	0
	•						•	
72	0	1	0	0	1	0	0	0
•	•							
80	0	1	0	1	0	0	0	0
•	•							
128	1	0	0	0	0	0	0	0
	•							
144	1	0	0	1	0	0	0	0
•								
254	1	1	1	1	1	1	1	0
255	1	1	1	1	1	1	1	1

4.4.2 Byte 7, Module Data Width Continued: This byte will be left at 00h if the original module data width is less than 256 Bits wide. If the width is more than 255, then this byte will be used in conjunction with byte 6.

Module Data Width Cont.	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0(+)	0	0	0	0	0	0	0	0
256(+)	0	0	0	0	0	0	0	1
512(+)	0	0	0	0	0	0	1	Х
1024(+)	0	0	0	0	0	1	Х	Х
2048(+)	0	0	0	0	1	X	X	Х
•								

4.5 Byte 8, Module Interface Levels: This field describes the module's voltage interface:

Voltage Interface	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
5.0 Volt/TTL	0	0	0	0	0	0	0	0
LVTTL	0	0	0	0	0	0	0	1
HSTL 1.5 V	0	0	0	0	0	0	1	0
SSTL 3.3 V	0	0	0	0	0	0	1	1
SSTL 2.5 V	0	0	0	0	0	1	0	0
TBD	0	0	0	0	0	1	0	1
TBD	0	0	0	0	0	1	1	0
	1	1	1	1	1	1	1	1

4.6 Byte 9, SDRAM Cycle time (tCYC): This byte defines the minimum cycle time for the SDRAM Module at the highest CAS Latency, CAS Latency=X, defined in byte 18. If other CAS latencies are supported, then the associated minimum cycle times are not related in this version of the SPD standard. At this time of publication, proposals are being made to widen the standard to relate cycle times at lower CAS Latencies. Byte 9, Cycle time for CAS Latency = X, is split into two nibbles: the higher order nibble (Bits 4 through 7) designate the cycle time to a granularity of 1 ns; the value presented by the lower order nibble (Bits 0 through 3) has a granularity of 1/10 ns and is added to the value designated by the higher nibble. For example, if

Bits 7:4 are and Bits 3:0 are then the cycle time is 1010 0101 (10 ns) + (0.5 ns) = 10.5 ns

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0			
	•		SDRAM	Cycle Time S	Subfield A: ts 4 through	_\	•				
					ts 4 through	7)					
Undefined	0	0	0	0							
1 ns	0	0	0	1							
2 ns	0	0	1	0							
3 ns	0	0	1	1							
4 ns	0	1	0	0							
5 ns	0	1	0	1		SEE Subfield Table B					
6 ns	0	1	1	0							
7 ns	0	1	1	1							
8 ns	1	0	0	0							
9 ns	1	0	0	1							
10 ns	1	0	1	0							
11 ns	1	0	1	1							
12 ns	1	1	0	0							
13 ns	1	1	0	1							
14 ns	1	1	1	0							
15 ns	1	1	1	1							
	•		SDRAM (Cycle Time S	Subfield B:						
			Tenths of	of ns (Bits 0	through 3)						
+0 ns					0	0	0	0			
+0.1 ns					0	0	0	1			
+0.2 ns					0	0	1	0			
+0.3 ns					0	0	1	1			
+0.4 ns					0	1	0	0			
+0.5 ns		SEE	Subfield ta	ble A	0	1	0	1			
+0.6 ns					0	1	1	0			
+0.7 ns					0	1	1	1			
+0.8 ns					1 0 0 0 1 0 0 1						
+0.9 ns											
RFU	_				1	0	1	0			
Undefined	1	1	1	1	1	1	1	1			

4.7 Byte 10, SDRAM Access time from Clock (tAC): This byte defines the maximum clock to data out for the module. This is the Clock to data out specification at the highest given CAS Latency specified/depicted in byte 18 of this SPD specification/standard. If other CAS latencies are supported, then the associated Maximum Clock Access times are not related in this version of the SPD standard. At this time of publication, proposals are being made to widen the standard to relate tAC's at lower CAS Latencies.

The byte is split into two nibbles: the higher order nibble (Bits 4 through 7) designate the cycle time to a granularity of 1 ns; the value presented by the lower order nibble (Bits 0 through 3) has a granularity of 1/10 ns and is added to the value designated by the higher nibble. For example, if

Bits 7:4 are and Bits 3:0 are then the cycle time is 1001 0000 (9 ns) + (0.0 ns) = 9.0 ns

1001	0000		+ (0.0 113)										
Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0					
		Access time											
		A: Units of r			ough 7)								
Undefined	0	0	0	0									
1 ns	0	0	0	1									
2 ns	0	0	1	0	_								
3 ns	0	0	1	1									
4 ns	0	1	0	0									
5 ns	0	1	0	1		SEE S	Subfield Tab	le B					
6 ns	0	1	1	0									
7 ns	0	1	1	1									
8 ns	1	0	0	0									
9 ns	1	0	0	1									
10 ns	1	0	1	0									
11 ns	1	0	1	1									
12 ns	1	1	0	0									
13 ns	1	1	0	1									
14 ns	1	1	1	0									
15 ns	1	1	1	1									
	SDRAM	1 Access time	e from CLK	•	•								
	Subfield	B: Tenths	of ns (Bits 0	through 3)									
+0 ns					0	0	0	0					
+0.1 ns					0	0	0	1					
+0.2 ns					0	0	1	0					
+0.3 ns					0	0	1	1					
+0.4 ns					0	1	0	0					
+0.5 ns		SEE Sub	ofield table	A	0	1	0	1					
+0.6 ns					0	1	1	0					
+0.7 ns					0	1	1	1					
+0.8 ns					1	0	0	0					
+0.9 ns					1	0	0	1					
RFU					1	0	1	0					
					1.	1.	1.	1.					
Undefined	1	1	1	1	1	1	1	1					

4.8 Byte 11, Module Configuration type: This field describes the module's error detection and or correction schemes:

Error Det/Cor	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
None	0	0	0	0	0	0	0	0
Parity	0	0	0	0	0	0	0	1
ECC	0	0	0	0	0	0	1	0
TBD	0	0	0	0	0	0	1	1
TBD	0	0	0	0	0	1	0	0
TBD	0	0	0	0	0	1	0	1
TBD	0	0	0	0	0	1	1	0
TBD	1	1	1	1	1	1	1	1

4.9 Byte 12, Refresh Rate/Type: This field describes the module's refresh rate and type:

, ,				,,				
Refresh Period	Bit 7, Self Re- fresh Flag	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Normal (15.625 us)	0	0	0	0	0	0	0	0
Reduced (.25x)3.9 us	0	0	0	0	0	0	0	1
Reduced (.5x)7.8 us	0	0	0	0	0	0	1	0
Extended (2x)31.3 us	0	0	0	0	0	0	1	1
Extended (4x)62.5 us	0	0	0	0	0	1	0	0
Extended (8x)125 us	0	0	0	0	0	1	0	1
TBD	0	0	0	0	0	1	1	0
TBD	0	0	0	0	0	1	1	1
TBD	0	0	0	0	1	0	0	0
TBD	0	0	0	0	1	0	0	1
		Self I	Refresh Er	ntries				
Normal (15.625 us)	1	0	0	0	0	0	0	0
Reduced (0.25x)3.9 us	1	0	0	0	0	0	0	1
Reduced (0.5x)7.8 us	1	0	0	0	0	0	1	0
Extended (2x)31.3 us	1	0	0	0	0	0	1	1
Extended (4x)62.5 us	1	0	0	0	0	1	0	0
Extended (8x)125 us	1	0	0	0	0	1	0	1
TBD	1	0	0	0	0	1	1	0
TBD								
TBD								
TBD	1	1	1	1	1	1	1	0
TBD	1	1	1	1	1	1	1	1

4.10 Byte 13, SDRAM width, Primary SDRAM: Bits 0–6 of this byte relate the primary data SDRAM's width; Bit 7 is a flag which is set to "1" when there is a 2nd physical bank on the module which is of different size from the 1st physical bank. Bit 7 set to "1" indicates that the 2nd physical bank's data RAMs are 2X the width of those on the 1st physical bank. If there is a second physical bank of same size and organization as the first, then Bit 7 remains as "0" and error checking SDRAM width for both banks is expressed using Bits 0–6. The primary SDRAM is that which is used for data; examples of primary (data) SDRAM widths are x4, x8, x16, x32. Note that if the module is made with SDRAMs which provide for data and error checking e.g. x9, x18, x36, then it is also designated in this field. Examples of SDRAM DIMM using 1 and 2 banks of symmetrical and asymmetrical size:

	Physical Bank 1	Physical Bank 2	Physical Bank 1	Physical Bank 2	Possible (16Mb based)	Byte 13
Module Width	Primary SDRAM Width	Primary SDRAM Width	Error Checking SDRAM Width	Error Checking SDRAM Width	Module Density	Contents
x72	x9	N/A		N/A	16 MB	0000 1001
x72	x8	N/A	x8	N/A	16 MB	0000 1000
x72	x16	N/A	x4	N/A	8 MB	0001 0000
x72	x8	x8	x8	x8	32 MB	0000 1000
x64	x8	x16	N/A	N/A	24 MB	1000 1000

		Subfield A	: Data SDR	AM Width				
Data SDRAM Width	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
N/A		0	0	0	0	0	0	0
1	1	0	0	0	0	0	0	1
:	1	:	:	:	:	:	:	:
4	1	0	0	0	0	1	0	0
:		:	:	:	:	:	:	:
8		0	0	0	1	0	0	0
9		0	0	0	1	0	0	1
:	See Subfield B	:	:	:	:	:	:	:
15		0	0	0	1	1	1	1
16		0	0	1	0	0	0	0
17		0	0	1	0	0	0	1
:		:	:	:	:	1	:	:
32		0	1	0	0	0	0	0
:		:	:	:	:	:	:	:
36		0	1	0	0	1	0	0
:		:	:	:	:	:	:	:
127		1	1	1	1	1	1	1
	Subfield	B: Bank 2	Data SDR	AM Width M	lultiplier			
Bank 2 Data SDRAM Width Multiplier	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
No Bank 2 -OR- Bank 2 uses same width SDRAM as bank 1	0			S	ee Subfield	A	•	•
Bank 2 SDRAM is 2X the Width of Bank 1 SDRAM	1							

4.11 Byte 14, Error Checking SDRAM data width: If the module incorporates error checking and if the primary data SDRAM does not include these Bits; i.e. there are separate error checking SDRAMs, then the error checking SDRAM's width is expressed in this byte. Bits 0-6 of this byte relate the error checking SDRAMs width; Bit 7 is a flag which is set to "1" when there is a 2nd physical bank on the module which is of different size from the 1st physical bank. Bit 7 set to "1" indicates that Bank 2's error checking RAMs are 2X the width of those on the 1st physical bank. If there is a second physical bank of same size and organization as the first, then Bit 7 remains as "0" and error checking SDRAM width for both physical banks is expressed using Bits 0-6. Examples of error checking SDRAM widths with 1 and 2 physical banks of Symmetric and Asymmetric sizing include:

	Physical Bank 1	Physical Bank 2	Physical Bank 1	Physical Bank 2	Possible (16Mb based)	Byte 13
Module Width	Primary SDRAM Width	Primary SDRAM Width	Error Checking SDRAM Width	Error Checking SDRAM Width	Module Density	Contents
x72	x9	N/A		N/A	16 MB	0000 0000
x72	x8	N/A	x8	N/A	16 MB	0000 1000
x72	x16	N/A	x4	N/A	8 MB	0000 0100
x72	x8	x8	x8	x8	32 MB	0000 1000
x72	x8	x16	x8	x16	24 MB	1000 1000
x80	x8	x16	x8	x16	24 MB	1000 1000

	S	Subfield A: E	Error Check	ing SDRAM	1 Width			
Error Checking SDRAM Width	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
N/A		0	0	0	0	0	0	0
1		0	0	0	0	0	0	1
:		:	:	:	:	:	:	:
4		0	0	0	0	1	0	0
:		:	:	:	:	:	i i	:
8		0	0	0	1	0	0	0
9		0	0	0	1	0	0	1
:	See Subfield B	:	:	:	:	:	i i	:
15		0	0	0	1	1	1	1
16		0	0	1	0	0	0	0
17		0	0	1	0	0	0	1
:		:	:	:	:	:	:	:
32		0	1	0	0	0	0	0
:		:	:	:	:	:	:	:
36		0	1	0	0	1	0	0
:		:	:	:	:	:	:	:
63		1	1	1	1	1	1	1
	Subfield B	B: Bank 2 E	rror Checki	ng SDRAM	Width Multi	plier		
Bank 2 Error Checking SDRAM Width Multi- plier	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
No Bank 2 -OR- Bank 2 uses same width SDRAM as bank 1	0				See Subfi	eld A		
Bank 2 SDRAM is 2X the Width of Bank 1 SDRAM	1							

4.12 Byte 15, as determined by the limiting part on the assembly, SDRAM Device Attributes: Minimum Clock Delay, Back to Back Random Column Accesses. Note that SDRAM architecture can be gained with this parameter. A latency of 1 for random writes denotes Pipelined SDRAM and a latency of 2 for random writes denotes Prefetch SDRAMs:

Number of Clocks	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
3	0	0	0	0	0	0	1	1
4	0	0	0	0	0	1	0	0
5	0	0	0	0	0	1	0	1
255	1	1	1	1	1	1	1	1

4.13 Byte 16, SDRAM Device Attributes, Burst Lengths Supported: This byte describes which various programmable burst lengths are supported by the devices on the module. If the bit is "0", then that Burst Length is supported on the module; If the bit is "0", then that burst length is not supported by the module.

Ī	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
	Burst Length = Page	TBD	TBD	TBD	Burst Length = 8	Burst Length = 4	Burst Length = 2	Burst Length = 1
ĺ	1 or 0	0	0	0	1 or 0	1 or 0	1 or 0	1 or 0

4.14 Byte 17, SDRAM Device Attributes, Number of Banks on the discrete SDRAM Device: This byte details how many banks are on each discrete SDRAM installed onto the module:

Number of Banks	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
3	0	0	0	0	0	0	1	1
4	0	0	0	0	0	1	0	0
5	0	0	0	0	0	1	0	1
255	1	1	1	1	1	1	1	1

4.15 Byte 18, SDRAM Device Attributes, CAS# Latency: This byte describes which of the programmable CAS# Latencies are supported by the Module. If the bit is "1", then that CAS# Latency is supported on the module; If the bit is "0", then that CAS# Latency is not supported by the module. Bytes 9,10,23–26 all relate CAS Latency dependent timings.

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
TBD		CAS# La- tency = 6					
0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0

4.16 Byte 19, SDRAM Device Attributes, CS# Latency: This byte describes which of the programmable CS# Latencies are acceptable for the Module. If the bit is "1", then that CS# Latency is supported on the module; If the bit is "0", then that CS# Latency is not supported by the module.

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
TBD	CS# La- tency = 6	CS# La- tency = 5	CS# La- tency = 4	CS# La- tency = 3	CS# La- tency = 2	CS# La- tency = 1	CS# La- tency = 0
0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0

4.17 Byte 20, SDRAM Device Attributes, WE# Latency: This byte describes which of the programmable WE# Latencies are acceptable for the Module. If the bit is "1", then that WE# Latency is supported on the module; If the bit is "0", then that WE# Latency is not supported by the module.

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
TBD	WE# La- tency = 6	WE# La- tency = 5	WE# La- tency = 4	WE# La- tency = 3	WE# La- tency = 2	WE# La- tency = 1	WE# La- tency = 0
0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0

4.18 Byte 21, SDRAM Module Attributes: This byte depicts various aspects of the module. It details various unrelated but critical elements pertinent to the module. A given module characteristic is detailed in the designated bit; if the aspect is TRUE, then the bit is "1". Conversely, if the aspect is FALSE, then the designated bit is "0".

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
TBD	*Redundant Addressing	Differential Clock Input	Registered DQMB Inputs	Buffered DQMB In- puts	On- Card PLL (Clock)	**Registered Ad- dress and Control Inputs	**Buffered Address and Control In- puts
0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0

- Redundant addressing implies the use of SDRAMs having the same address depth (e.g. 4Mx4 mixed with 4Mx16) in the same 8 byte quad word, but having different RAS/CAS addressing and/or different numbers of device banks. Actual implementation is not yet determined.
- ** Address, RAS, CAS, WE, CKE, CS
 4.19 Byte 22, SDRAM Device Attributes, General: This byte depicts various aspects of the SDRAMs on the module. It details various unrelated but critical elements pertinent to the SDRAMs. A given SDRAM characteristic is detailed in the designated bit; unless otherwise specified, if the aspect is TRUE, then the bit is "1". Conversely, if the aspect is FALSE, then the designated bit is "0".

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
TBD	TBD	*Upper Vcc tolerance: 0=10% 1=5%	*Lower Vcc tolerance: 0=10% 1=5%	Supports Write1/Read Burst 0=false 1=true	Supports Pre- charge All 0=false 1=true	Supports Auto-Pre- charge 0=false 1=true	Supports Early RAS# Prechar- ge 0=false 1=true
0	0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0	1 or 0

Tolerance refers to the voltage range under which the SDRAMs operate.

4.20 Byte 23: Minimum Clock Cycle Time at reduced CAS latency, X-1: The highest CAS latency identified in byte 18 is X and the timing values associated with CAS Latency 'X' are found at byte locations 9 and 10. Byte 23 denotes the minimum cycle time at CAS X-1.

For example, if byte 18 denotes CAS latencies of 1–3, then X is 3 and X–1 is 2. Byte 23 then denotes the minimum cycle time at CAS Latency = 2.

Byte 23 is split into two nibbles: the higher order nibble (Bits 4 through 7) designate the cycle time to a granularity of 1 ns; the value presented by the lower order nibble (Bits 0 through 3) has a granularity of 1/10 ns and is added to the value designated by the higher nibble. For example, if

Bits 7:4 are and Bits 3:0 are then the cycle time is 1001 (9 ns) + (0.5 ns) = 9.5 ns

	0101	()	(0.0 110)								
Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0			
		SE	RAM Minin	num Cycle ti	me @ CL X	-1:					
		Sul	ofield A: In ι	units of ns (E	Bits 4 throug	h 7)					
Undefined	0	0	0	0							
1 ns/16 ns	0	0	0	1	1						
2 ns/17 ns	0	0	1	0	1						
3 ns/18 ns	0	0	1	1	1						
4 ns	0	1	0	0	1						
5 ns	0	1	0	1	1	SEE	Subfield Ta	ıble B			
6 ns	0	1	1	0	1						
7 ns	0	1	1	1	1						
8 ns	1	0	0	0	1						
9 ns	1	0	0	1	1						
10 ns	1	0	1	0	1						
11 ns	1	0	1	1	1						
12 ns	1	1	0	0	1						
13 ns	1	1	0	1	1						
14 ns	1	1	1	0	1						
15 ns	1	1	1	1							
		SE	RAM Minin	num Cycle ti	me @ CL X	-1:					
		Sub	ofield B: Te	enths of ns (E	Bits 0 throug	ıh 3)					
+0 ns					0	0	0	0			
+0.1 ns					0	0	0	1			
+0.2 ns					0	0	1	0			
+0.3 ns					0	0	1	1			
+0.4 ns					0	1	0	0			
+0.5 ns		SEE	Subfield tal	ble A	0	1	0	1			
+0.6 ns					0	1	1	0			
+0.7 ns					0 1 1 1						
+0.8 ns					1	0	0	0			
+0.9 ns					1	0	0	1			
RFU		1 0 1									
				-							
Undefined	1	1	1	1	1	1	1	1			

4.21 Byte 24: Maximum Data Access Time from Clock (tAC) at Reduced CAS Latency, X-1: The highest CAS latency identified in byte 18 is X.. Byte 24 denotes the maximum access time from Clock at CAS Latency X-1.

For example, if byte 18 denotes supported CAS latencies of 1–3, then X is 3 and X–1 is 2. Byte 24 then denotes the maximum data access time from CLK at CAS Latency 2.

The byte is split into two nibbles: the higher order nibble (Bits 4 through 7) designate the cycle time to a granularity of 1 ns; the value presented by the lower order nibble (Bits 0 through 3) has a granularity of 1/10 ns and is added to the value designated by the higher nibble. For example, if

Bits 7:4 are and Bits 3:0 are then the cycle time is 1001 (9 ns) + (0.5 ns) = 9.5 ns0101

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
				s time from (
		Subfield	d A: Units of	nanosecon	ds (Bits 4 th	rough 7)		
Undefined	0	0	0	0				
1 ns/16 ns	0	0	0	1	1			
2 ns/17 ns	0	0	1	0	1			
3 ns/18 ns	0	0	1	1	1			
4 ns	0	1	0	0	1			
5 ns	0	1	0	1	1	SEE	Subfield Ta	able B
6 ns	0	1	1	0	1			
7 ns	0	1	1	1	1			
8 ns	1	0	0	0	1			
9 ns	1	0	0	1	1			
10 ns	1	0	1	0	1			
11 ns	1	0	1	1	1			
12 ns	1	1	0	0	1			
13 ns	1	1	0	1	1			
14 ns	1	1	1	0	1			
15 ns	1	1	1	1	1			
	•	SD	RAM Acces	s time from	CLK @ CL	X-1		
		Sub	ofield B: Te	enths of ns (E	Bits 0 throug	jh 3)		
+0 ns					0	0	0	0
+0.1 ns					0	0	0	1
+0.2 ns					0	0	1	0
+0.3 ns					0	0	1	1
+0.4 ns					0	1	0	0
+0.5 ns		SEE	Subfield ta	ble A	0	1	0	1
+0.6 ns	_				0	1	1	0
+0.7 ns	_				0	1	1	1
+0.8 ns	_				1	0	0	0
+0.9 ns	_				1	0	0	1
RFU	_				1	0	1	0
Undefined	1	1	1	1	1	1	1	1

4.22 Byte 25: Minimum Clock Cycle time at reduced CAS latency, X-2: The highest CAS latency identified in byte 18 is X.. Byte 25 denotes the minimum cycle time at CAS Latency X-2.

For example, if byte 18 denotes CAS latencies of 1–3, then X is 3 and X–2 is 1. Byte 25 then denotes the minimum cycle time at CAS Latency 1.

Byte 25 is split into two parts: the higher order Bits (Bits 2 through 7) designate the cycle time to a granularity of 1 ns; the value presented by the lower order Bits (0 through 1) has a granularity of 1/4 ns and is added to the value designated by the higher Bits. For example, if

Bits 7:2 are 011001 and Bits 1:0 are 011001 bits 7:2 are and Bits 1:0 are 1100001 and Bits 1:0 are 1100001 then the cycle time is 1100001 then the cycle time is 1100001 then the cycle time is 1100001 changes (33 ns) + (.75 ns) = 33.75 ns

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
	SDRAM M	linimum Cycl	e time @ CL throu	X-2: Subfield igh 7)	A: In units of	f ns (Bits 2		
Undefined	0	0	0	0	0	0		
1 ns	0	0	0	0	0	1		
2 ns	0	0	0	0	1	0		
3 ns	0	0	0	0	1	1		
4 ns	0	0	0	1	0	0	1	
5 ns	0	0	0	1	0	1	1	
6 ns	0	0	0	1	1	0	See Su	ıbfield B
7 ns	0	0	0	1	1	1	1	
8 ns	0	0	1	0	0	0	1	
9 ns	0	0	1	0	0	1	1	
10 ns	0	0	1	0	1	0	1	
:	:	:	:	:	:	:	1	
:	:	:	:	:	:	:	1	
61 ns	1	1	1	1	0	1	1	
62 ns	1	1	1	1	1	0		
63 ns	1	1	1	1	1	1		
							Cycle time Field B: Q	Minimum @ CL = X-2 uarters of ns nrough 1)
+0 ns							0	0
+0.25 ns	+0.25 ns							
+0.5 ns	1	1	0					
+0.75 ns							1	1

4.23 Byte 26: Maximum Data Access Time from Clock (tAC) at reduced CAS Latency, X-2: The highest CAS latency identified in byte 18 is X.. Byte 26 denotes the maximum access time from Clock at CAS Latency X-2.

For example, if byte 18 denotes supported CAS latencies of 1-3, then X is 3 and

X-2 is 1. Byte 26 then denotes the maximum data access time from CLK at CAS Latency 1.

The byte is split into two parts: the higher order Bits (Bits 2 through 7) designate the cycle time to a granularity of 1 ns; the value presented by the lower order nibble (Bits 0 through 1) has a granularity of 1/4 ns and is added to the value designated by the higher nibble. For example, if

Bits 7:2 are and Bits 1:0 are then the max access time is 001001 01 (9 ns) + (0.25 ns) = 9.25 ns

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
		SDRAM	Access time	from Clock @	CL X-2:			
		Subfield A: U	Jnits of nanos	seconds (Bits	4 through 7)			
Undefined	0	0	0	0	0	0		
1 ns	0	0	0	0	0	1		
2 ns	0	0	0	0	1	0		
3 ns	0	0	0	0	1	1		
4 ns	0	0	0	1	0	0		
5 ns	0	0	0	1	0	1		
6 ns	0	0	0	1	1	0	See Su	bfield B
7 ns	0	0	0	1	1	1		
8 ns	0	0	1	0	0	0		
9 ns	0	0	1	0	0	1	1	
10 ns	0	0	1	0	1	0		
:	:	:	:	:	:	:		
:	:	:	:	:	:	:	1	
61 ns	1	1	1	1	0	1	1	
62 ns	1	1	1	1	1	0		
63 ns	1	1	1	1	1	1		
								ccess time @ CL X-2
							Subfield B: ns (Bits 0	Quarters of through 1)
+0 ns							0	0
+0.25 ns			0	1				
+0.5 ns			1	0				
+0.75 ns							1	1

4.24 Byte 27, Minimum Row Precharge Time (tRP): Byte 27 is used to designate the modules minimum Row Precharge time. The decode for this SPD byte is as follows:

Minimum Row Precharge time (Nanoseconds)	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
25	0	0	0	1	1	0	0	1
26	0	0	0	1	1	0	1	0
27	0	0	0	1	1	0	1	1
28	0	0	0	1	1	1	0	0
29	0	0	0	1	1	1	0	1
30	0	0	0	1	1	1	1	0
31	0	0	0	1	1	1	1	1
32	0	0	1	0	0	0	0	0
33	0	0	1	0	0	0	0	1
34	0	0	1	0	0	0	1	0
35	0	0	1	0	0	0	1	1
36	0	0	1	0	0	1	0	0
					•	•		
					•	•		
127	0	1	1	1	1	1	1	1
128	1	0	0	0	0	0	0	0
						•		
						-		
254	1	1	1	1	1	1	1	0
255	1	1	1	1	1	1	1	1

4.25 Byte 28, Minimum Row Active to Row Active Delay (tRRD): This field describes the minimum required delay between different row activations:

Min Row active to Row Active Delay (Nanosec- onds)	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
					•	•		
19	0	0	0	1	0	0	1	1
20	0	0	0	1	0	1	0	0
21	0	0	0	1	0	1	0	1
22	0	0	0	1	0	1	1	0
23	0	0	0	1	0	1	1	1
24	0	0	0	1	1	0	0	0
25	0	0	0	1	1	0	0	1
				•			•	
127	0	1	1	1	1	1	1	1
128	1	0	0	0	0	0	0	0
	•							
254	1	1	1	1	1	1	1	0
255	1	1	1	1	1	1	1	1

4.26 Byte 29, Minimum RAS to CAS Delay (tRCD): This SPD byte describes the minimum delay required between assertions of RAS\ and CAS\.

Minimum RAS to CAS Delay (Nanoseconds)	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
25	0	0	0	1	1	0	0	1
26	0	0	0	1	1	0	1	0
27	0	0	0	1	1	0	1	1
28	0	0	0	1	1	1	0	0
29	0	0	0	1	1	1	0	1
30	0	0	0	1	1	1	1	0
31	0	0	0	1	1	1	1	1
32	0	0	1	0	0	0	0	0
33	0	0	1	0	0	0	0	1
34	0	0	1	0	0	0	1	0
35	0	0	1	0	0	0	1	1
36	0	0	1	0	0	1	0	0
								-
127	0	1	1	1	1	1	1	1
128	1	0	0	0	0	0	0	0
254	1	1	1	1	1	1	1	0
255	1	1	1	1	1	1	1	1

4.27 Byte 30: tRAS: This byte identifies the minimum RAS pulse width:

Minimum RAS Pulse Width (Nanoseconds)	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Undefined	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
2	0	0	0	0	0	0	1	0
25	0	0	0	1	1	0	0	1
26	0	0	0	1	1	0	1	0
27	0	0	0	1	1	0	1	1
28	0	0	0	1	1	1	0	0
29	0	0	0	1	1	1	0	1
30	0	0	0	1	1	1	1	0
31	0	0	0	1	1	1	1	1
32	0	0	1	0	0	0	0	0
33	0	0	1	0	0	0	0	1
34	0	0	1	0	0	0	1	0
35	0	0	1	0	0	0	1	1
36	0	0	1	0	0	1	0	0
	•							
127	0	1	1	1	1	1	1	1
128	1	0	0	0	0	0	0	0
254	1	1	1	1	1	1	1	0
255	1	1	1	1	1	1	1	1

4.28: Byte 31: Density of each bank on module: This byte describes the density of each physical bank on the SDRAM DIMM. This byte will have at least one Bit set to "1" to represent at least one banks density. If there are more than one bank on the module (as represented in byte #5) and they have the same density, then only one bit is set in this field. If the module has more than one bank of different sizes then more than one bit will be set; each bit set for each density represented. For example:

# Banks	Densiy of Bank 1	Density of bank 2	Byte 31 contents
1	32MByte	N/A	0000 1000
2	32MByte	32MBbyte	0000 1000
2	32MByte	16MByte	0000 1100

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Density	512MByte	256MByte	128MByte	64MByte	32MByte	16Mbyte	2GB/8MB	1GB/4MB
N/Y	0/1	0/1	0/1	0/1	0/1	0/1	0/1	0/1

4.29 Byte 32, Address and Command signal input setup time before clock: This field describes the input setup time before the rising edge of clock. Since this value can be either negative or positive, provisions have been made to accommodate both. If one byte starts with a Zero in Bit 7, then the input setup time is positive. If the byte starts with a One in Bit 7, then the value is negative.

For example, if

Value Byte Contents 2.5 ns 0010 0101 -2.5 ns 1010 0101

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0			
Input Setup Time before Clock: Subfield A: Units of nanoseconds (Bits 4 through 7)											
Less than 1 ns, >0	0	0	0	0		,					
1 ns	0	0	0	1	1						
2 ns	0	0	1	0							
3 ns	0	0	1	1							
4 ns	0	1	0	0							
5 ns	0	1	0	1		SEE	Subfield Ta	ble B			
6 ns	0	1	1	0							
7 ns	0	1	1	1							
Less than zero, > (-1 ns)	1	0	0	0							
-1 ns	1	0	0	1							
-2 ns	1	0	1	0							
-3 ns	1	0	1	1							
-4 ns	1	1	0	0							
-5 ns	1	1	0	1							
-6 ns	1	1	1	0							
-7 ns	1	1	1	1							
		Su	Input Set bfield B: Tei	up Time beforths of ns (B	ore Clock: its 0 througl	h 3)					
+/-0 ns					0	0	0	0			
+/-0.1 ns					0	0	0	1			
+/-0.2 ns					0	0	1	0			
+/-0.3 ns					0	0	1	1			
+/-0.4 ns					0	1	0	0			
+/-0.5 ns		SEE	Subfield ta	ble A	0	1	0	1			
+/-0.6 ns					0	1	1	0			
+/-0.7 ns					0	1	1	1			
+/-0.8 ns					1	0	0	0			
+/-0.9 ns					1	0	0	1			
RFU					1	0	1	0			
			•								
RFU	1	1	1	1	1	1	1	1			

4.30 Byte 33, Address and Command signal input hold times after clock: This field describes the input hold time after the rising edge of clock. Since this value can be either negative or positive, provisions have been made to accommodate both. If one byte starts with a Zero in Bit 7, then the input setup time is positive. If the byte starts with a One in Bit 7, then the value is negative. For example, if

Value Byte Contents 0010 0101 2.5 ns 1010 0101 -2.5 ns

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0				
	Input Hold times after Clock: Subfield A: Units of nanoseconds (Bits 4 through 7)											
Less than 1 ns, >0	0	0	0	0	(= 1.0 1 1.1							
1 ns	0	0	0	1	1							
2 ns	0	0	1	0	1							
3 ns	0	0	1	1								
4 ns	0	1	0	0								
5 ns	0	1	0	1		SEE	Subfield Ta	ble B				
6 ns	0	1	1	0								
7 ns	0	1	1	1								
Less than zero, > (-1 ns)	1	0	0	0								
-1 ns	1	0	0	1								
-2 ns	1	0	1	0	1							
-3 ns	1	0	1	1								
-4 ns	1	1	0	0	1							
-5 ns	1	1	0	1								
-6 ns	1	1	1	0								
-7 ns	1	1	1	1								
		Su	Input Ho	old times aftenths of ns (B	er Clock:	h 3)						
+/-0 ns			5. 10.	10 01 110 (2	0	0	0	0				
+/-0.1 ns					0	0	0	1				
+/-0.2 ns					0	0	1	0				
+/-0.3 ns					0	0	1	1				
+/-0.4 ns					0	1	0	0				
+/-0.5 ns		SEE	Subfield tal	ble A	0	1	0	1				
+/-0.6 ns	1				0	1	1	0				
+/-0.7 ns	1				0	1	1	1				
+/-0.8 ns					1	0	0	0				
+/-0.9 ns	1				1	0	0	1				
RFU					1	0	1	0				
RFU	1	1	1	1	1	1	1	1				

4.31 Byte 34, Data Signal input setup time before clock: This field describes the input setup time before the rising edge of clock. Since this value can be either negative or positive, provisions have been made to accomodate both. If one byte starts with a Zero in Bit 7, then the input setup time is positive. If the byte starts with a One in Bit 7, then the value is negative. For example, if

Value Byte Contents 2.5 ns 0010 0101 -2.5 ns 1010 0101

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0			
		Subfield	Input Setul A: Units of	up Time befo f nanosecon	ore Clock: ds (Bits 4 th	rough 7)					
Less than 1 ns, >0	0	0	0	0							
1 ns	0	0	0	1	1						
2 ns	0	0	1	0	1						
3 ns	0	0	1	1							
4 ns	0	1	0	0							
5 ns	0	1	0	1		SEE	Subfield Ta	ble B			
6 ns	0	1	1	0							
7 ns	0	1	1	1							
Less than zero, > (-1 ns)	1	0	0	0							
-1 ns	1	0	0	1							
-2 ns	1	0	1	0							
-3 ns	1	0	1	1							
-4 ns	1	1	0	0	1						
-5 ns	1	1	0	1							
-6 ns	1	1	1	0							
-7 ns	1	1	1	1							
		Su	Input Set bfield B: Ter	up Time bef	ore Clock: its 0 througl	h 3)					
+/-0 ns					0	0	0	0			
+/-0.1 ns					0	0	0	1			
+/-0.2 ns					0	0	1	0			
+/-0.3 ns					0	0	1	1			
+/-0.4 ns					0	1	0	0			
+/-0.5 ns		SEE	Subfield tal	ble A	0	1	0	1			
+/-0.6 ns					0	1	1	0			
+/-0.7 ns		0 1 1									
+/-0.8 ns					1	0	0	0			
+/-0.9 ns					1	0	0	1			
RFU					1	0	1	0			
RFU	1	1	1	1	1	1	1	1			

4.32 Byte 35, Data Signal Input hold times after clock: This field describes the input hold time after the rising edge of clock. Since this value can be either negative or positive, provisions have been made to accommodate both. If one byte starts with a Zero in Bit 7, then the input setup time is positive. If the byte starts with a One in Bit 7, then the value is negative. For example, if

Value Byte Contents 2.5 ns 0010 0101 -2.5 ns 1010 0101

Nanoseconds	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0					
	Input Hold times after Clock: Subfield A: Units of nanoseconds (Bits 4 through 7)												
Less than 1 ns, >0	0	0	0	0	us (bits + ti)	ilougii 7)							
1 ns	0	0	0	1	4								
2 ns	0	0	1	0	4								
3 ns	0	0	1	1									
4 ns	0	1	0	0									
5 ns	0	1	0	1		SEE	Subfield Ta	hle B					
6 ns	0	1	1	0		OLL	- Subileiu ia	able b					
7 ns	0	1	1	1									
Less than zero, > (-1 ns)	1	0	0	0									
-1 ns	1	0	0	1									
-2 ns	1	0	1	0									
-3 ns	1	0	1	1									
-4 ns	1	1	0	0	-								
-5 ns	1	1	0	1									
-6 ns	1	1	1	0									
-7 ns	1	1	1	1									
		_	Input Ho	old times aft	er Clock:								
		Su	bfield B: Tei	nths of ns (B				1					
+/-0 ns					0	0	0	0					
+/-0.1 ns					0	0	0	1					
+/-0.2 ns					0	0	1	0					
+/-0.3 ns					0	0	1	1					
+/-0.4 ns					0	1	0	0					
+/-0.5 ns		SEE	Subfield ta	ble A	0	1	0	1					
+/-0.6 ns					0	1	1	0					
+/-0.7 ns					0	1	1	1					
+/-0.8 ns					1	0	0	0					
+/-0.9 ns					1	0	0	1					
RFU					1	0	1	0					
RFU	1	1	1	1	1	1	1	1					

- 4.33 Bytes 36-40, Superset information. Reserved for VCSDRAM. These bytes are reserved for Virtual Channel SDRAM.
- 4.33.1 Byte 41: SDRAM Device Minimum Active to Active/Auto Refresh Time (t_{RC}) This byte identifies the minimum active to active or auto refresh time (tRC).

Minimum Active to Active/Auto Refresh Time (nanoseconds)	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Hex
Undefined	0	0	0	0	0	0	0	0	00
1	0	0	0	0	0	0	0	1	01
2	0	0	0	0	0	0	1	0	02
25	0	0	0	1	1	0	0	1	19
26	0	0	0	1	1	0	1	0	1A
27	0	0	0	1	1	0	1	1	1B
28	0	0	0	1	1	1	0	0	1C
29	0	0	0	1	1	1	0	1	1D
30	0	0	0	1	1	1	1	0	1E
31	0	0	0	1	1	1	1	1	1F
32	0	0	1	0	0	0	0	0	20
33	0	0	1	0	0	0	0	1	21
34	0	0	1	0	0	0	1	0	22
35	0	0	1	0	0	0	1	1	23
36	0	0	1	0	0	1	0	0	24
127	0	1	1	1	1	1	1	1	7F
128	1	0	0	0	0	0	0	0	80
254	1	1	1	1	1	1	1	0	FE
Undefined	1	1	1	1	1	1	1	1	FF

- 4.34 Bytes 42-61, Superset information. See the appropriate Superset appendices.
- 4.33.2 Byte 60, ESDRAM Attributes: See Appendix H
- 4.35 Byte 61, Superset Technology: See Appendix H
- 4.36 Byte 62, Serial Presence Detect Revision: As SPD definition may be updated, it becomes necessary to identify the version of SPD which is being depicted:

SPD Revision	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Initial Release	0	0	0	0	0	0	0	0
REV 1	0	0	0	0	0	0	0	1
REV 2	0	0	0	0	0	0	1	0
REV 3.	0.	0.	0.	0.	0.	0.	1.	1.

- 4.37 Byte 64-71, Manufacturers JEDEC ID code per JEP-106E.
- 4.38 Byte 72, Manufacturing location: This byte indicates the modules manufacturing origin (module manufacturer specific) in ASCII format. Module manufacturers shall track the manufacturing location and its appropriate decode.
- 4.39 Byte 73-90, These bytes contain the module manufacturer's part number in ASCII format. Unused digits are coded as ASCII blanks (20h).
- 4.40 Byte 91–92, These bytes are used to identify the module revision codes in ASCII format. Module manufacturers shall track the revision codes and its appropriate decode.

- 4.41 Byte 93, This location contains the binary value of the year in which the module was manufactured. For example, year 1998 would be coded as 62h.
- 4.42 Byte 94, This location contains the binary value of the week of the year (1–52) during which the module was manufactured. For example, week 19 would be coded as 13h.
- 4.43 Byte 95-98, These bytes contain a unique module serial number. The supplier may use whatever decode method desired to maintain a unique serial number for each module. Bytes 95-98 must be coded such that bytes 64-72 and 93-98 will result in a unique serial number. One method of achieving this is by assigning a byte in the field from 95-98 as a tester ID byte and using the remaining bytes as a sequential serial number.
- 4.44 Byte 99–125, The module manufacturer may include any additional information into the module within these locations.
- 4.45 Byte 126–127, These bytes are reserved and cannot be allocated at any time. Data stored in this location is defined in the Intel PC SDRAM SPD specification.
- 4.46 Byte 128-255, These bytes are used by the manufacturer and are open for customer use.